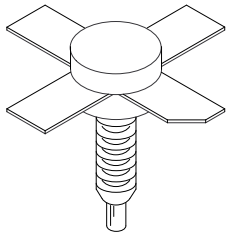
The RF Line
UHF Power Transistor

. . . designed primarily for wideband, large–signal output and driver amplifier stages to 1000 MHz.

- Designed for Class A Linear Power Amplifiers
- Specified 19 Volt, 1000 MHz Characteristics:
  Output Power — 7.0 Watts
  Power Gain — 9.0 dB Min, Small–Signal
- Built–In Matching Network for Broadband Operation
- Gold Metallization for Improved Reliability
- Diffused Ballast Resistors
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

MRA1000-7L

9.0 dB, TO 1000 MHz
7.0 WATTS BROADBAND
UHF POWER TRANSISTOR



CASE 145D–02, STYLE 1
(.380 SOE)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	28	Vdc
Collector–Base Voltage	V_{CBO}	50	Vdc
Emitter–Base Voltage	V_{EBO}	3.5	Vdc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	42 0.25	Watts W/°C
Operating Junction Temperature	T_J	200	°C
Storage Temperature Range	T_{stg}	–65 to +150	°C

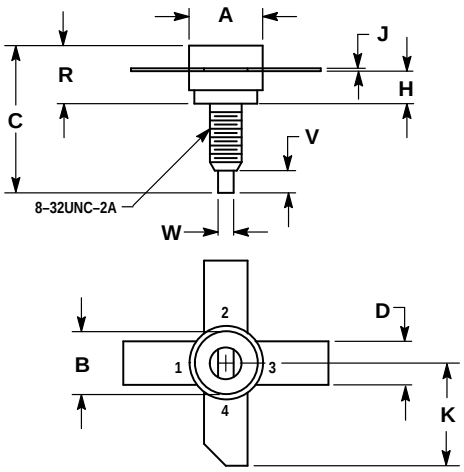
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (T_C = 70°C)	$R_{\theta JC}$	4.0	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I_C = 20 mA, I_B = 0)	$V_{(BR)CEO}$	28	—	—	Vdc
Collector–Emitter Breakdown Voltage (I_C = 20 mA, V_{BE} = 0)	$V_{(BR)CES}$	50	—	—	Vdc
Collector–Base Breakdown Voltage (I_C = 20 mA, I_E = 0)	$V_{(BR)CBO}$	50	—	—	Vdc
Emitter–Base Breakdown Voltage (I_E = 5.0 mA, I_C = 0)	$V_{(BR)EBO}$	3.5	—	—	Vdc
Collector Cutoff Current (V_{CB} = 19 V, I_E = 0)	I_{CBO}	—	—	15	mAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 1.0 A, V_{CE} = 5.0 V)	h_{FE}	20	—	90	—
DYNAMIC CHARACTERISTICS					
Output Capacitance (V_{CB} = 24 V, I_E = 0, f = 1.0 MHz)	C_{ob}	—	—	22	pF
FUNCTIONAL TESTS					
Common–Emitter Amplifier Small–Signal Gain (V_{CE} = 19 V, f = 1.0 GHz, I_C = 1.2 A)	G_{SS}	9.0	10	—	dB
Load Mismatch (V_{CE} = 19 V, I_C = 1.2 A, P_{out} = 7.0 W, f = 1.0 GHz, Load VSWR = ∞:1, All Phase Angles)	ψ	No Degradation in Output Power			
Overdrive (V_{CE} = 19 V, I_C = 1.2 A, f = 1.0 GHz) (No degradation)	$P_{in_{over}}$	—	—	3.5	W
Output Power, 1.0 dB Compression Point (V_{CE} = 19 V, f = 1.0 GHz, I_C = 1.2 A)	$P_{o1\ dB}$	7.0	—	—	W

PACKAGE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.320	0.385	9.28	9.77
B	0.320	0.330	8.13	8.38
C	0.700	0.778	17.78	19.76
D	0.220	0.230	5.59	5.84
H	0.160	0.170	4.07	4.31
J	0.003	0.006	0.08	0.15
K	0.490	0.520	12.45	13.20
R	0.248	0.275	6.30	7.23
V	0.100	0.130	2.54	3.30
W	0.055	0.065	1.40	1.65

STYLE 1:
PIN 1. EMITTER
2. BASE
3. EMITTER
4. COLLECTOR

CASE 145D–02
ISSUE A

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